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10/772,863

JAN 04 2006

PATENT**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of:

Abdalla Aly Naem, et al.

Appln. No.: 10/772,863

Filed: February 4, 2004

For: METHOD OF FORMING A MOS
TRANSISTOR WITH A LAYER OF
SILICON GERMANIUM CARBON (as
amended)

Group Art Unit: 2823

Examiner: William M. Brewster

SUPPLEMENTAL AMENDMENT IN
RESPONSE TO EXAMINER'S PROPOSED
AMENDMENT RECEIVED DECEMBER 22,
2005INTRODUCTORY COMMENTSCommissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the Examiner's Proposed Amendment received on December 22, 2005, please amend the above-identified application as indicated in the following:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper; and

Remarks which begin on page 5 of this paper.

William M. Brewster
WILLIAM M. BREWSTER
PRIMARY EXAMINER

13 JAN 2006

OK to Enter

AMENDMENT IN RESPONSE TO EXAMINER'S
PROPOSED AMENDMENT RECEIVED DECEMBER 22, 2005Atty. Docket No. 100-19810
(P05402-D01)